

Description

This 30V,20A N-Channel MOSFET in a TO-252 Plastic Package.

Features

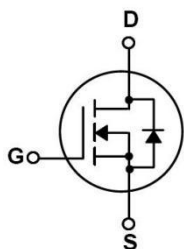
- Low $R_{DS(on)}$
- Low gate charge
- Low C_{rss}
- Fast speed switching
- Halogen-free Product

Applications

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products

V_{DSS}	$R_{DS(on)}$ Typ	I_D
30V	11m Ω	20A

Equivalent Circuit & Pinning



PIN1 : Gate PIN 2 : Drain PIN 3 : Source PIN 4 : Drain

Absolute Maximum Ratings(Ta=25°C)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current		$I_D(T_c=25^{\circ}\text{C})$	20	A
Gate-Source Voltage		V_{GS}	± 20	V
Avalanche Current		I_{AS}	10.4	A
Single Pulsed Avalanche Energy		E_{AS}	130	mJ
Power Dissipation		$P_D(T_c=25^{\circ}\text{C})$	55	W
Junction Temperature Range		T_j	150	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55~150	$^{\circ}\text{C}$
Maximum Junction-to-Ambient	Steady-State	$R_{\theta JA}$	62.7	$^{\circ}\text{C/W}$
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	2.3	

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1.0	μA
		$V_{DS}=30V$ $T_J=150^{\circ}\text{C}$			50	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20.0A$		11	13	$m\Omega$
		$V_{GS}=4.5V$ $I_D=10.0A$		16	18	$m\Omega$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1	1.8	3	V
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_F=1.0A$		0.7	1.2	V
Signal Source Resistance	R_g	$F=1\text{MHz}$		1.67		Ω
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0\text{MHz}$		666		pF
Output Capacitance	C_{oss}			26		
Reverse Transfer Capacitance	C_{rss}			63		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=15V$ $V_{GS}=10V$ $R_L=0.75\Omega$ $R_{GEN}=3.0\Omega$		7		ns
Turn-On Rise Time	t_r			13.5		
Turn-Off Delay Time	$t_{d(off)}$			18.5		
Turn-Off Fall Time	t_f			4		

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	$V_{DS}=15V \quad V_{GS}=10V$ $I_D=20.0A$		14		nC
Total Gate Charge	$Q_{g(4.5V)}$			6.5		
Gate-Source Charge	Q_{gs}			3		
Gate-Drain Charge	Q_{gd}			2.5		

Electrical Characteristic Curve

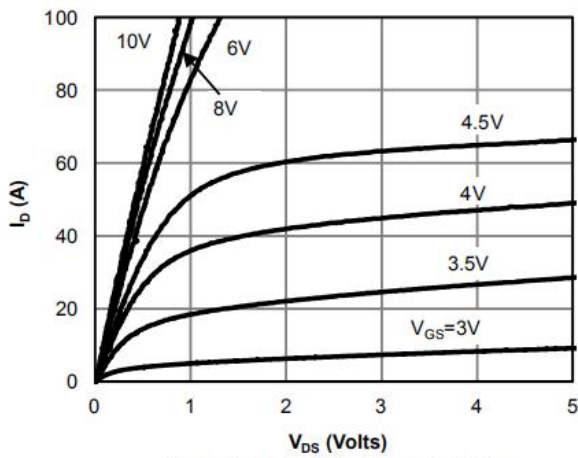


Figure 1: On-Region Characteristics

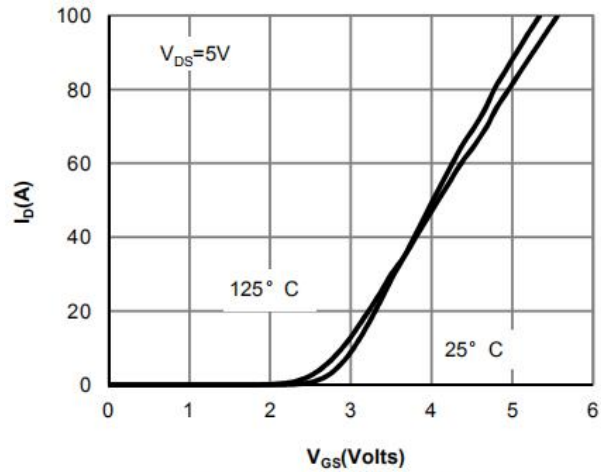


Figure 2: Transfer Characteristics

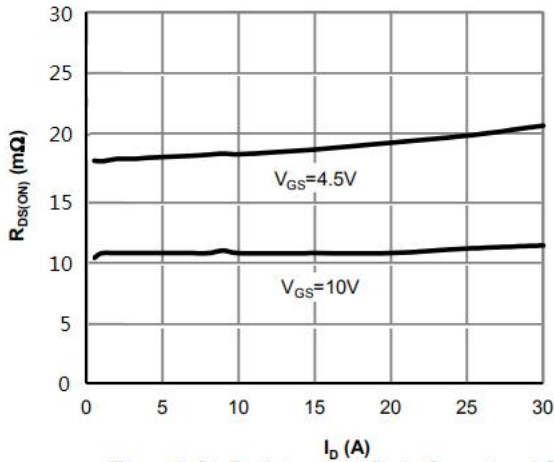


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

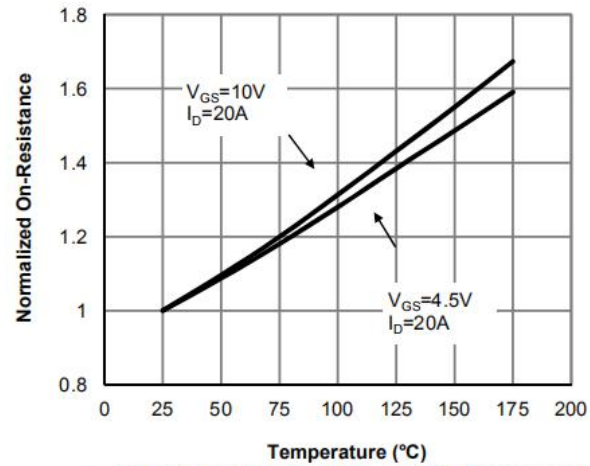


Figure 4: On-Resistance vs. Junction Temperature

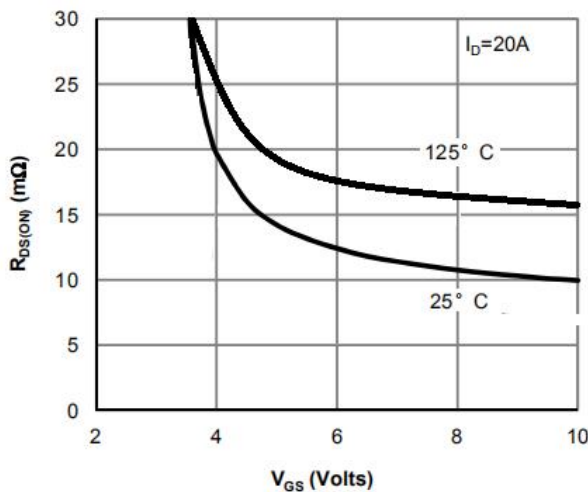


Figure 5: On-Resistance vs. Gate-Source Voltage

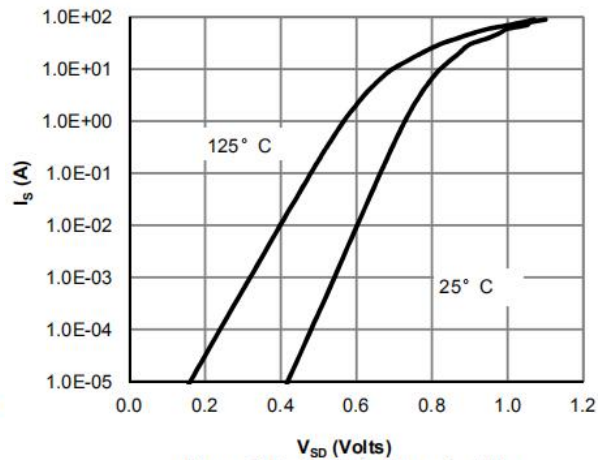
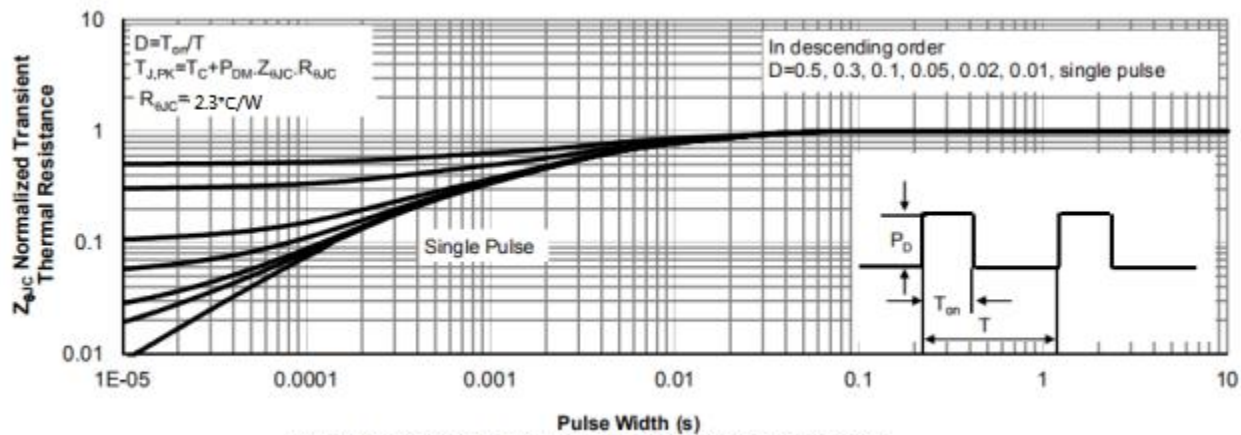
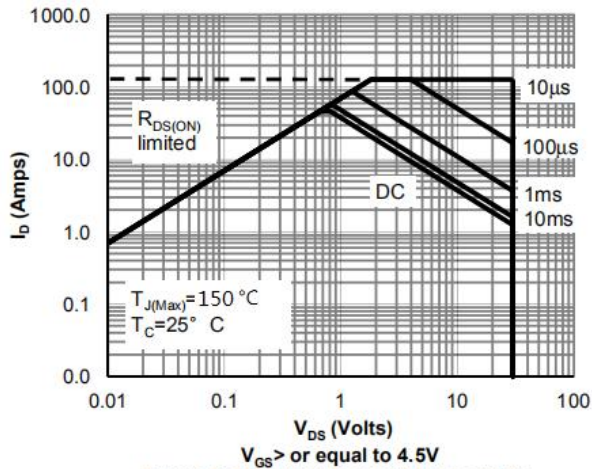
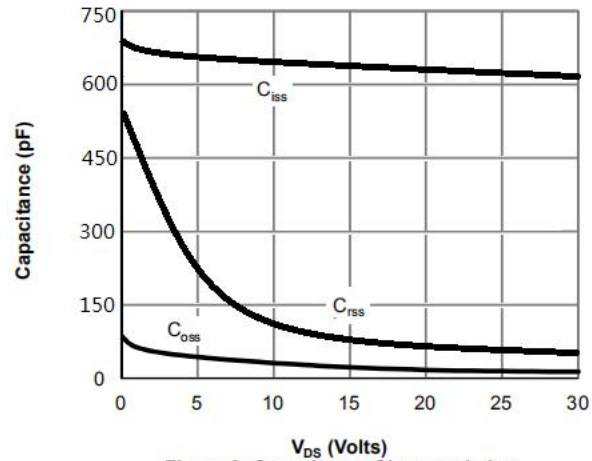
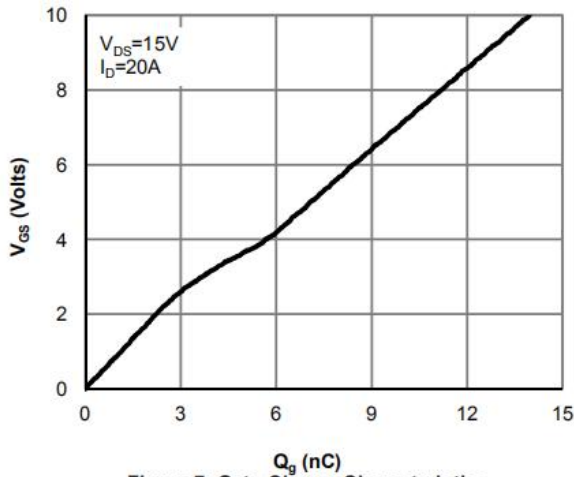
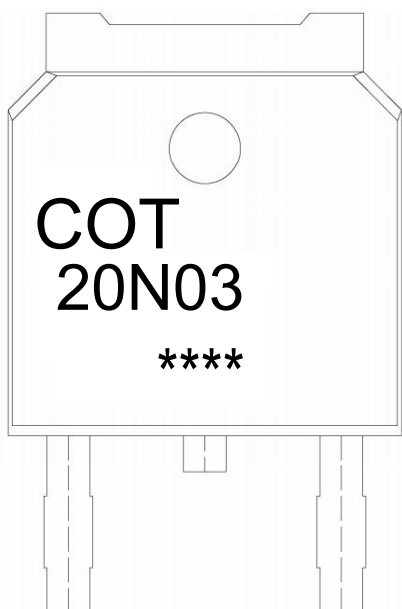


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve



Marking Instructions



Note:

COT: Company Code.

20N03: Product Type.

****: Lot No. Code, code change with Lot No.

Packaging SPEC.

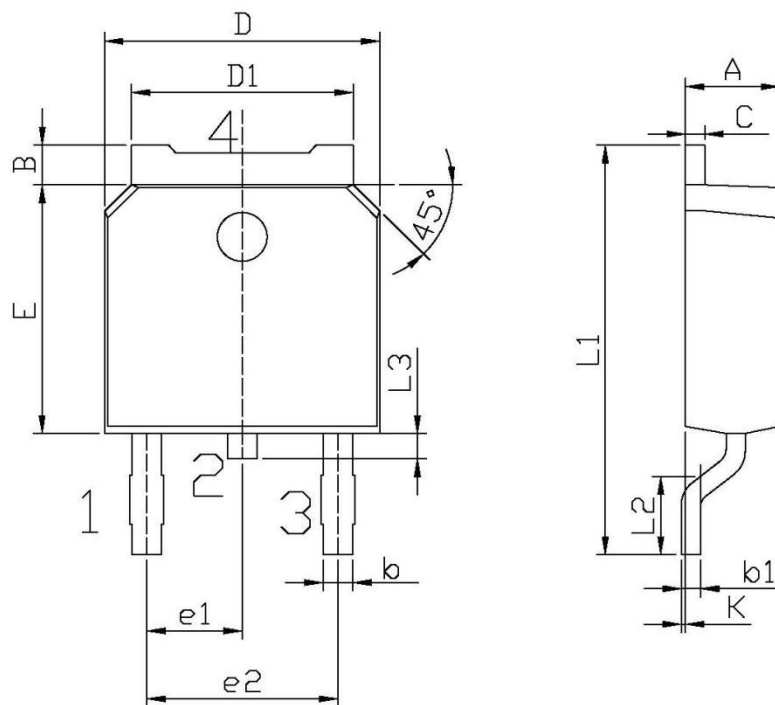
REEL INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13" ×16	360×360×50	380×335×366

TUBE INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

Package Outline Dimensions



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252